

# H7N1002LD, H7N1002LS, H7N1002LM

Silicon N Channel MOS FET  
High Speed Power Switching

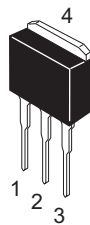
REJ03G1131-0700  
(Previous: ADE-208-1573E)  
Rev.7.00  
Apr 07, 2006

## Features

- Low on-resistance  
 $R_{DS(on)} = 8 \text{ m}\Omega$  typ.
- Low drive current
- Available for 4.5 V gate drive

## Outline

RENESAS Package code: PRSS0004AE-A  
(Package name: LDKPAK (L) )



H7N1002LD

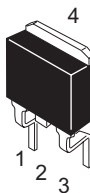
RENESAS Package code: PRSS0004AE-B  
(Package name: LDKPAK (S)-(1) )



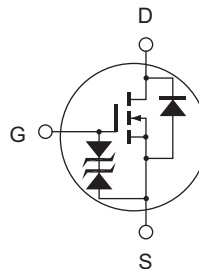
H7N1002LS

1. Gate
2. Drain
3. Source
4. Drain

RENESAS Package code: PRSS0004AE-C  
(Package name: LDKPAK (S)-(2) )



H7N1002LM



## Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Drain to source voltage	V <sub>DSS</sub>	100	V
Gate to source voltage	V <sub>GSS</sub>	±20	V
Drain current	I <sub>D</sub>	75	A
Drain peak current	I <sub>D (pulse)</sub> <sup>Note 1</sup>	300	A
Body to drain diode reverse drain current	I <sub>DR</sub>	75	A
Avalanche current	I <sub>AP</sub> <sup>Note 3</sup>	50	A
Avalanche energy	E <sub>AR</sub> <sup>Note 3</sup>	166	mJ
Channel dissipation	P <sub>ch</sub> <sup>Note 2</sup>	100	W
Channel temperature	T <sub>ch</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

- Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1%  
 2. Value at Tc = 25°C  
 3. Value at Tch = 25°C, Rg ≥ 50 Ω

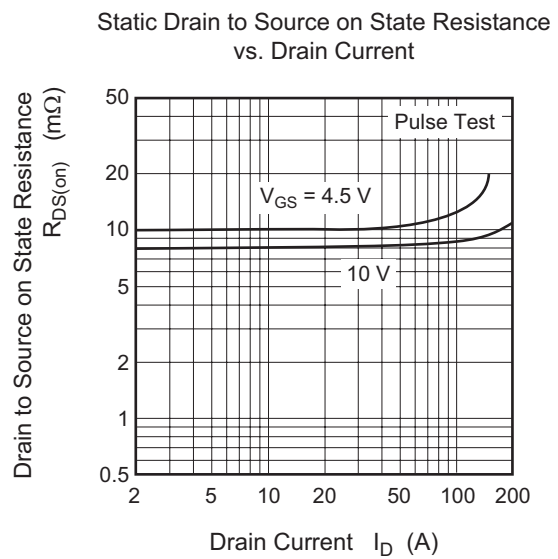
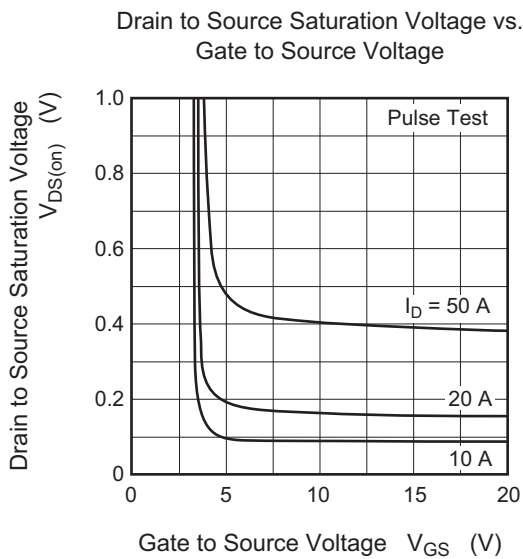
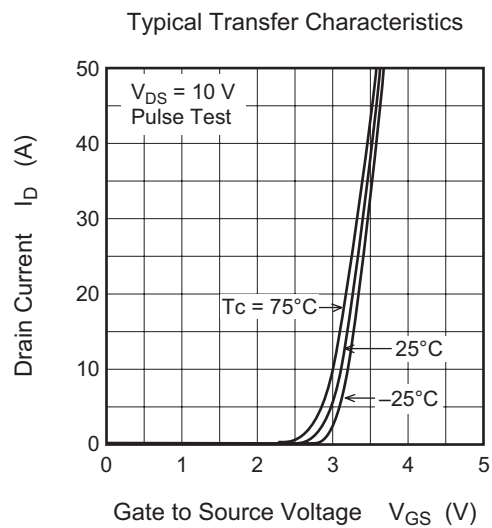
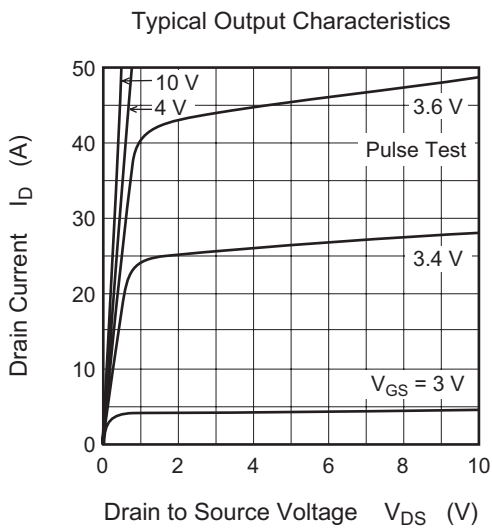
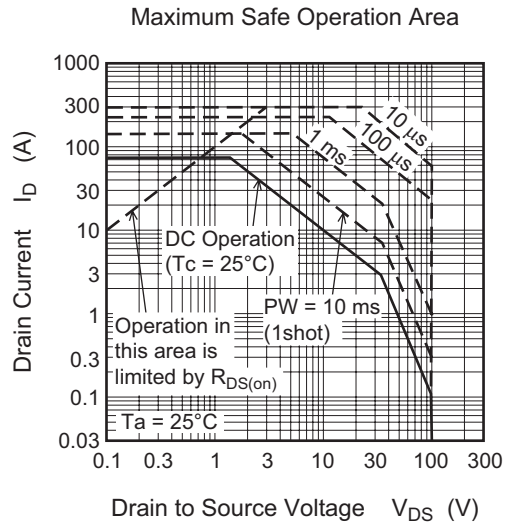
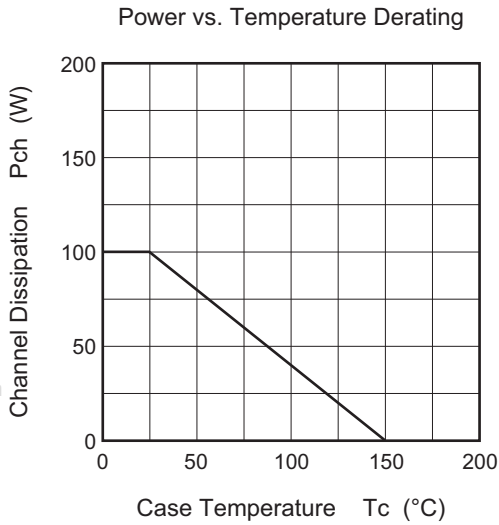
## Electrical Characteristics

(Ta = 25°C)

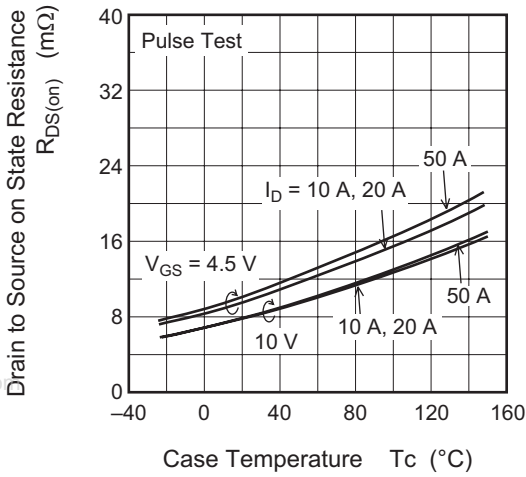
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	V <sub>(BR) DSS</sub>	100	—	—	V	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0
Gate to source breakdown voltage	V <sub>(BR) GSS</sub>	±20	—	—	V	I <sub>G</sub> = ±100 μA, V <sub>DS</sub> = 0
Gate to source leak current	I <sub>GSS</sub>	—	—	±10	μA	V <sub>GS</sub> = ±16 V, V <sub>DS</sub> = 0
Zero gate voltage drain current	I <sub>DSS</sub>	—	—	10	μA	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0
Gate to source cutoff voltage	V <sub>GS (off)</sub>	1.0	—	2.5	V	I <sub>D</sub> = 1 mA, V <sub>DS</sub> = 10 V <sup>Note 4</sup>
Static drain to source on state resistance	R <sub>DS (on)</sub>	—	8	10	mΩ	I <sub>D</sub> = 37.5 A, V <sub>GS</sub> = 10 V <sup>Note 4</sup>
		—	10	15	mΩ	I <sub>D</sub> = 37.5 A, V <sub>GS</sub> = 4.5 V <sup>Note 4</sup>
Forward transfer admittance	y <sub>fs</sub>	57	95	—	S	I <sub>D</sub> = 37.5 A, V <sub>DS</sub> = 10 V <sup>Note 4</sup>
Input capacitance	C <sub>iss</sub>	—	9700	—	pF	V <sub>DS</sub> = 10 V
Output capacitance	C <sub>oss</sub>	—	740	—	pF	V <sub>GS</sub> = 0
Reverse transfer capacitance	C <sub>rss</sub>	—	330	—	pF	f = 1 MHz
Total gate charge	Q <sub>g</sub>	—	155	—	nC	V <sub>DD</sub> = 50 V
Gate to source charge	Q <sub>gs</sub>	—	35	—	nC	V <sub>GS</sub> = 10 V
Gate to drain charge	Q <sub>gd</sub>	—	33	—	nC	I <sub>D</sub> = 75 A
Turn-on delay time	t <sub>d (on)</sub>	—	43	—	ns	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 37.5 A
Rise time	t <sub>r</sub>	—	245	—	ns	R <sub>L</sub> = 0.8 Ω
Turn-off delay time	t <sub>d (off)</sub>	—	130	—	ns	R <sub>g</sub> = 4.7 Ω
Fall time	t <sub>f</sub>	—	25	—	ns	
Body to drain diode forward voltage	V <sub>DF</sub>	—	0.93	—	V	I <sub>F</sub> = 75 A, V <sub>GS</sub> = 0
Body to drain diode reverse recovery time	t <sub>rr</sub>	—	70	—	ns	I <sub>F</sub> = 75 A, V <sub>GS</sub> = 0 di <sub>F</sub> /dt = 100 A/μs

- Note: 4. Pulse test

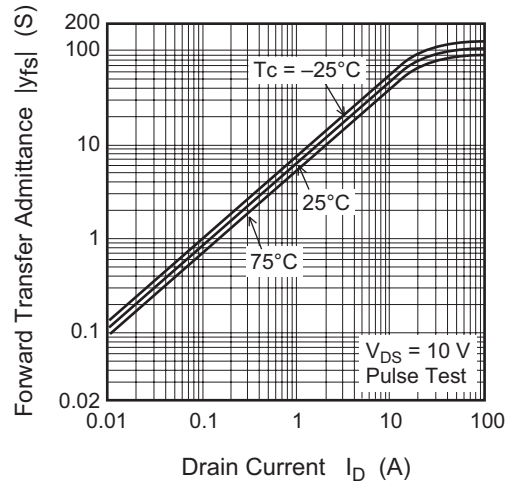
### Main Characteristics



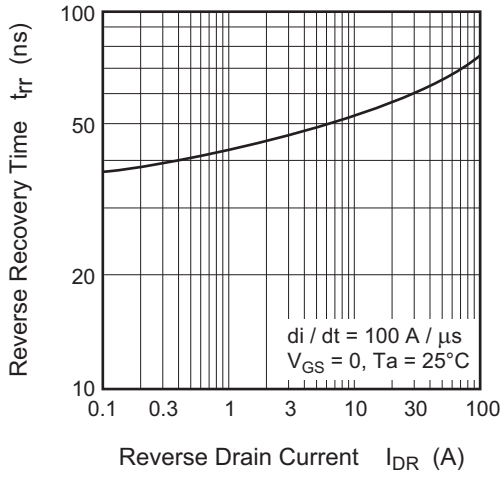
Static Drain to Source on State Resistance vs. Temperature



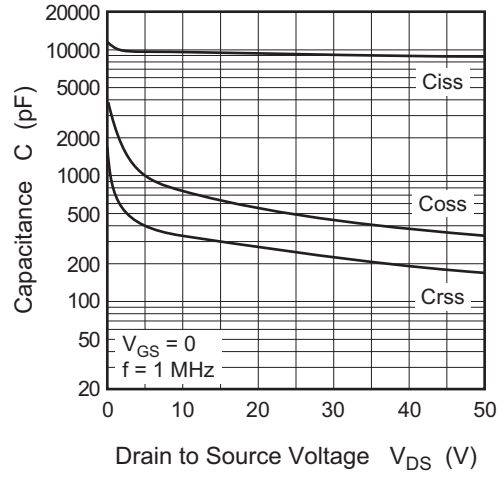
Forward Transfer Admittance vs. Drain Current



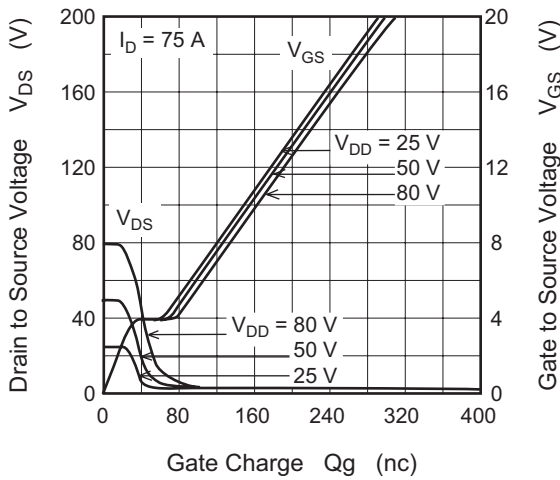
Body to Drain Diode Reverse Recovery Time



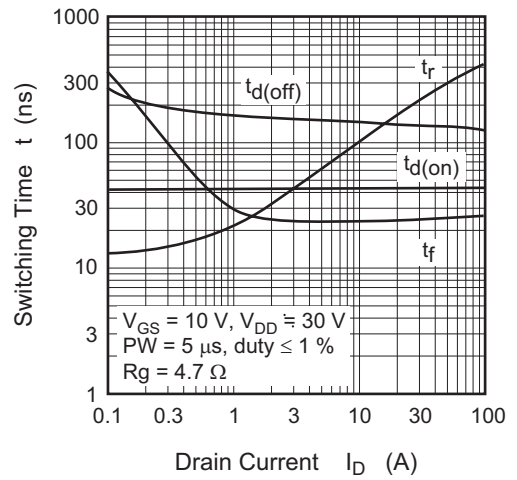
Typical Capacitance vs. Drain to Source Voltage

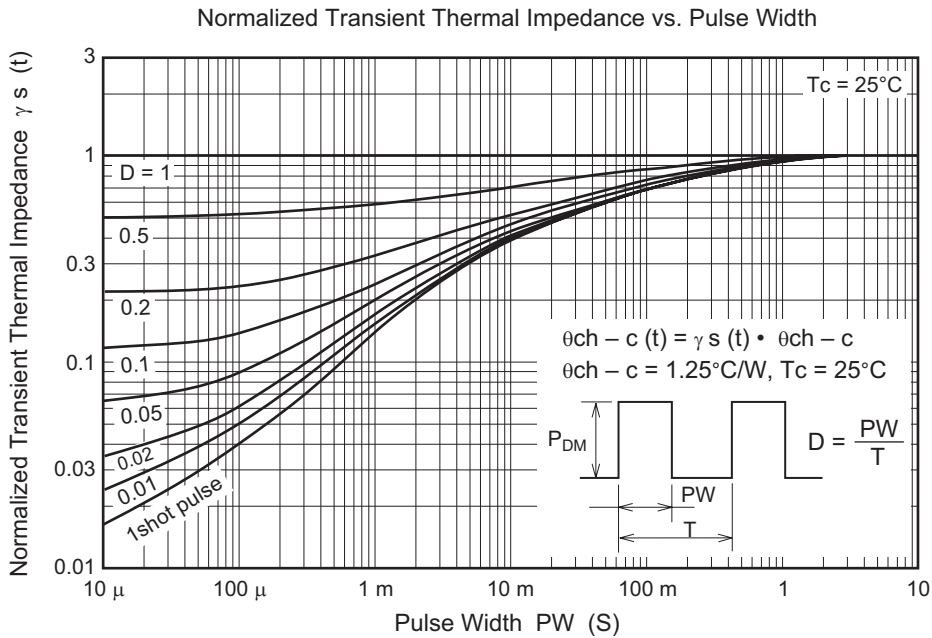
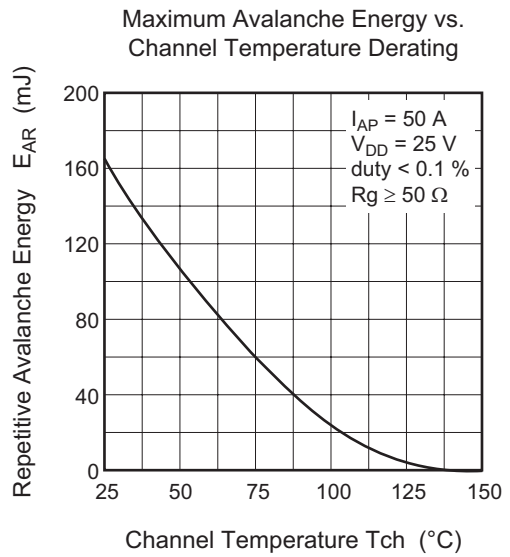
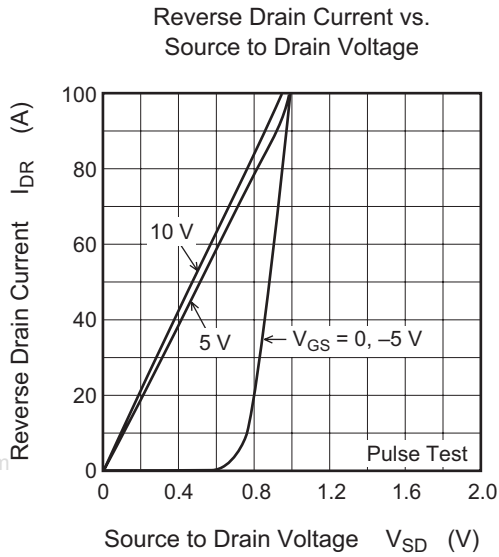


Dynamic Input Characteristics

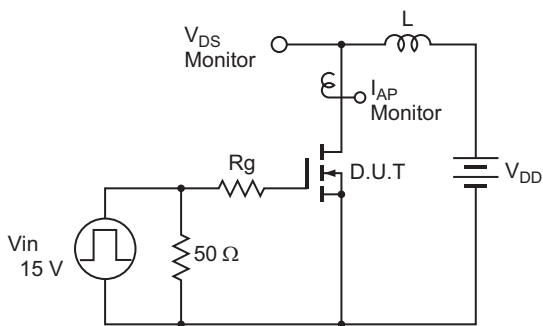


Switching Characteristics



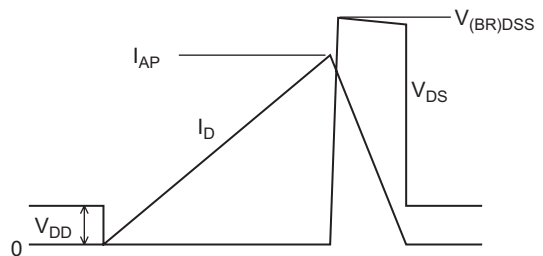


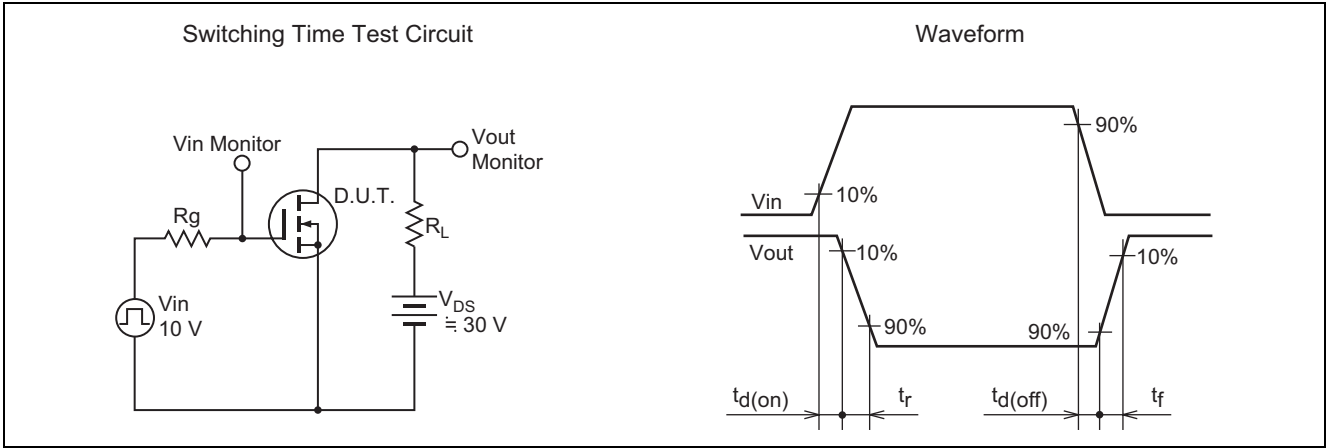
Avalanche Test Circuit



Avalanche Waveform

$$E_{AR} = \frac{1}{2} \cdot L \cdot I_{AP}^2 \cdot \frac{V_{DSS}}{V_{DSS} - V_{DD}}$$



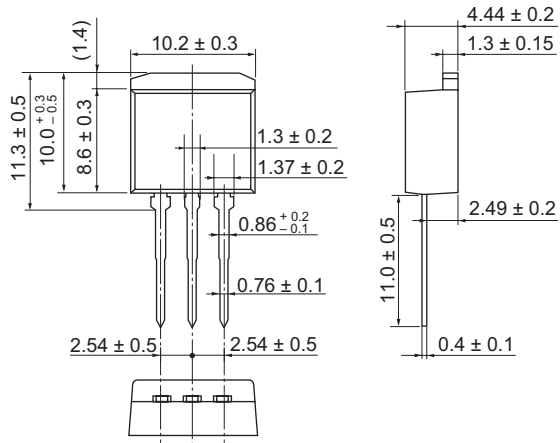


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Package Dimensions

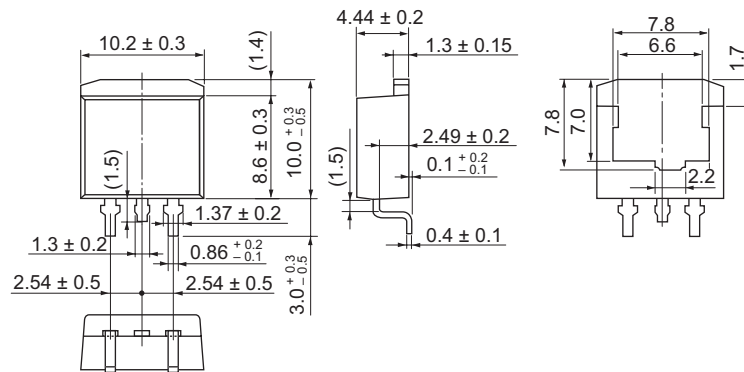
Package Name	JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
LDBPAK(L)	—	PRSS0004AE-A	LDBPAK(L) / LDBPAK(L)V	1.40g

Unit: mm



Package Name	JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
LDBPAK(S)-(1)	SC-83	PRSS0004AE-B	LDBPAK(S)-(1) / LDBPAK(S)-(1)V	1.30g

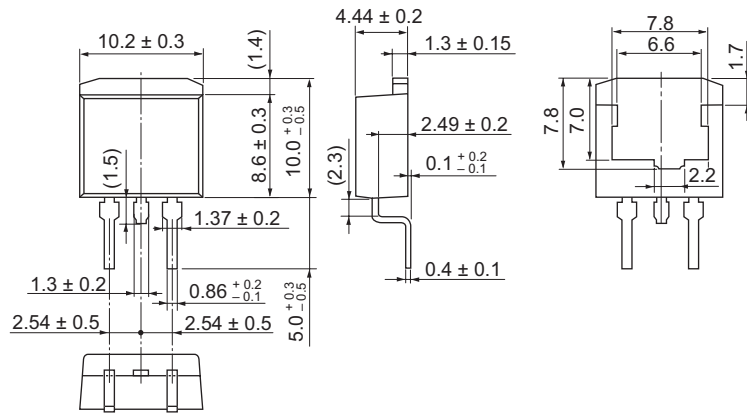
Unit: mm



## H7N1002LD, H7N1002LS, H7N1002LM

Package Name	JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
LDBPAK(S)-(2)	—	PRSS0004AE-C	LDBPAK(S)-(2) / LDBPAK(S)-(2)V	1.35g

Unit: mm



### Ordering Information

Part Name	Quantity	Shipping Container
H7N1002LD-E	500 pcs	Box (Conductive Sack)
H7N1002LSTL-E	1000 pcs	Taping
H7N1002LMTL-E	1000 pcs	Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.



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